



Monolithic Dual SPST CMOS Analog Switch

DESCRIPTION

The DG200B is a dual, single-pole, single-throw analog switch designed to provide general purpose switching of analog signals. This device is ideally suited for designs requiring a wide analog voltage range coupled with low on-resistance.

The DG200B is designed on Vishay Siliconix' improved PLUS-40 CMOS process. An epitaxial layer prevents latchup.

Each switch conducts equally well in both directions when on, and blocks up to 30 V peak-to-peak when off. In the on condition, this bi-directional switch introduces no offset voltage of its own.

FEATURES

- ± 15 V Input Signal Range
- 44 V Maximum Supply Ranges
- On-Resistance: 45 Ω
- TTL and CMOS Compatibility



RoHS³

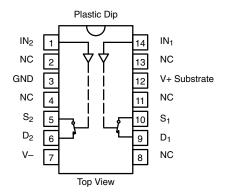
BENEFITS

- · Wide Dynamic Range
- Simple Interfacing
- Reduced External Component Count

APPLICATIONS

- · Servo Control Switching
- Programmable Gain Amplifiers
- Audio Switching
- · Programmable Filters

FUNCTIONAL BLOCK DIAGRAM AND PIN CONFIGURATION



TRUTH TABLE	
Logic	Switch
0	ON
1	OFF

 $\begin{array}{l} Logic \ "0" \leq 0.8 \ V \\ Logic \ "1" \geq 2.4 \ V \end{array}$

ORDERING INFORMATION						
Temp Range	Package	Part Number				
- 40 to 85 °C	14-Pin Plastic DIP	DG200BDJ DG200BDJ-E3				

^{*} Pb containing terminations are not RoHS compliant, exemptions may apply

Vishay Siliconix



ABSOLUTE MAXIMUM RATINGS $T_A = 25^{\circ}C$, unless otherwise noted						
Parameter		Limit	Unit			
V+ to V-		44				
GND to V-		25	V			
Digital Inputs ^a , V _S , V _D		(V-) - 2 V to (V+) + 2 V or 30 mA, whichever occurs first				
Current (Any Terminal) Continuous		30	mA			
Current S or D	(Pulsed at 1 ms, 10 % Duty Cycle Max)	100	l IIIA			
Storage Temperature		- 65 to 150	°C			
Power Dissipation (Package) ^b	14-Pin Plastic DIP ^c	470	mW			

Notes:

- a. Signals on S_X , D_X , or IN_X exceeding V+ or V- will be clamped by internal diodes. Limit forward diode current to maximum current ratings. b. All leads welded or soldered to PC Board.
- c. Derate 6.5 mW/°C above 25 °C.

SCHEMATIC DIAGRAM (TYPICAL CHANNEL)

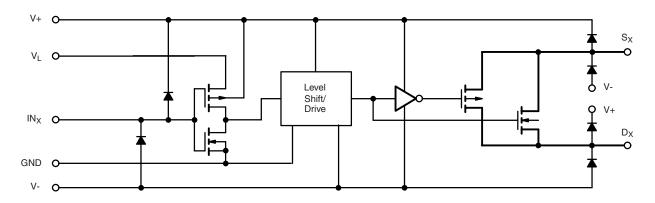


Figure 1.





Parameter		Test Conditions Unless Otherwise Specified V+ = 15 V, V- = - 15 V			Limits - 40 to 85 °C			
	Symbol	$V_{IN} = 2.4 \text{ V}, 0$		Temp ^b	Min ^c	Typ ^d	Max ^c	Unit
Analog Switch	├				L			
Analog Signal Range ^e	V _{ANALOG}			Full	- 15		15	V
Drain-Source On-Resistance	r _{DS(on)}	$V_D = \pm 10 \text{ V}, I_S = -1 \text{ mA}$		Room Full		45	85 100	Ω
Source Off Leakage Current	I _{S(off)}	$V_S = \pm 14 \text{ V}, V_D = \pm 14 \text{ V}$		Room Full	- 2 - 100	± 0.01	2 100	
Drain Off Leakage Current	I _{D(off)}	$V_D = \pm 14 \text{ V}, V_S = \mp 14 \text{ V}$		Room Full	- 2 - 100	± 0.01	2 100	nA
Channel On Leakage Current ^f	I _{D(on)}	$V_S = V_D = \pm 14 \text{ V}$		Room Full	- 2 - 200	± 0.1	2 200	
Digital Control								
Input Current with Input Voltage High	I	V _{IN} = 2.4 V		Room Full	- 0.5 - 1	0.0009		
	INH	V _{IN} = 15 V		Room Full		0.005	0.5 1	μА
Input Current with Input Voltage Low	I _{INL}	V _{IN} = 0 V		Room Full	- 0.5 - 1	- 0.0015		
Dynamic Characteristics								
Turn-On Time	t _{ON}	See Switching Time Test Circuit		Room		300	1000	nc
Turn-Off Time	t _{OFF}	See Switching Time	lest Circuit	Room		200	425	ns
Charge Injection	Q	$C_L = 1000 \text{ pF}, R_g = 0 \Omega, V_g = 0 \text{ V}$		Room		1		рС
Source Off Capacitance	C _{S(off)}	f = 140 kHz	V _S = 0 V	Room		5		nE
Drain Off Capacitance	C _{D(off)}	$V_{IN} = 5 V$	$V_D = 0 V$	Room		5		
Channel-On Capacitance	C _{D(on)} + C _{S(on)}	$V_S = V_D = 0 \text{ V}, V_{IN} = 0 \text{ V}$		Room		16		- pF
Off Isolation	OIRR	$V_{IN} = 5 \text{ V}, R_L = 75 \Omega$ $V_S = 2 \text{ V}, f = 1 \text{ MHz}$		Room		90		dB
Crosstalk (Channel-to-Channel)	X _{TALK}			Room		95		
Power Supplies	L .							
Positive Supply Current	l+	Both Channels On or Off V _{IN} = 0 V and 5.0 V		Room			50	
Negative Supply Current	I-			Room	- 10			μA

Notes:

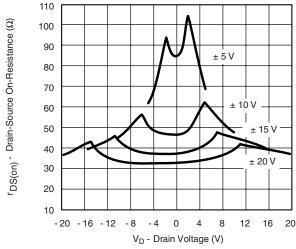
- a. Refer to PROCESS OPTION FLOWCHART.
- b. Room = 25 $^{\circ}$ C, Full = as determined by the operating temperature suffix.
- c. Typical values are for DESIGN AID ONLY, not guaranteed nor subject to production testing.
- d. The algebraic convention whereby the most negative value is a minimum and the most positive a maximum, is used in this data sheet.
- e. Guaranteed by design, not subject to production test.
- f. V_{IN} = input voltage to perform proper function.

Stresses beyond those listed under "Absolute Maximum Ratings" may cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those indicated in the operational sections of the specifications is not implied. Exposure to absolute maximum rating conditions for extended periods may affect device reliability.

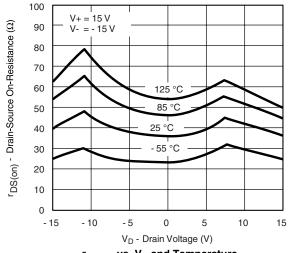
Vishay Siliconix



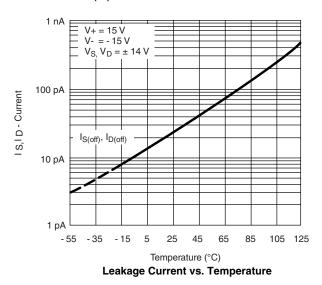
TYPICAL CHARACTERISTICS 25 °C, unless otherwise noted



 $r_{DS(on)}$ vs. V_D and Power Supply Voltages



r_{DS(on)} vs. V_D and Temperature

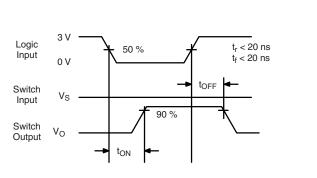


40 V+ = 22 V V - = -22 V30 T_A = 25 °C 20 I_{D(on)} S,I D - Current (pA) 10 I_{S(off)}, I_{D(off)} 0 - 10 - 20 - 30 - 40 - 10 - 5 0 20 - 20 - 15 5 10 15

Leakage Currents vs. Analog Voltage

TEST CIRCUITS

 V_O is the steady state output with switch on. Feedthrough via gate capacitance may result in spikes at leading and trailing edge of output waveform.



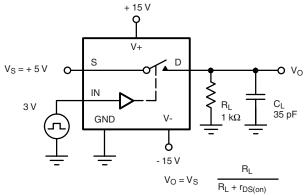
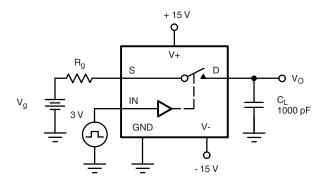
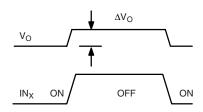


Figure 2. Switching Time



TEST CIRCUITS





 ΔV_O = measured voltage error due to charge injection The charge injection in coulombs is ΔQ = $C_L \; x \; \Delta V_O$

Figure 3. Charge Injection

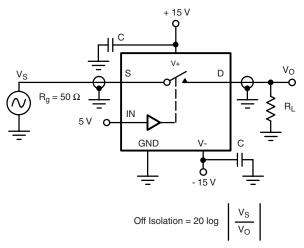


Figure 4. Off Isolation

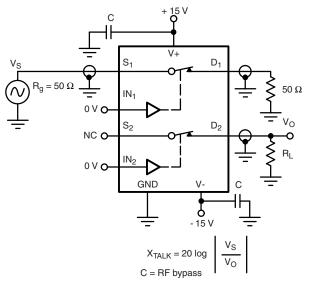


Figure 5. Channel-to-Channel Crosstalk

Vishay Siliconix maintains worldwide manufacturing capability. Products may be manufactured at one of several qualified locations. Reliability data for Silicon Technology and Package Reliability represent a composite of all qualified locations. For related documents such as package/tape drawings, part marking, and reliability data, see http://www.vishay.com/ppg?71357.



Vishay

Disclaimer

All product specifications and data are subject to change without notice.

Vishay Intertechnology, Inc., its affiliates, agents, and employees, and all persons acting on its or their behalf (collectively, "Vishay"), disclaim any and all liability for any errors, inaccuracies or incompleteness contained herein or in any other disclosure relating to any product.

Vishay disclaims any and all liability arising out of the use or application of any product described herein or of any information provided herein to the maximum extent permitted by law. The product specifications do not expand or otherwise modify Vishay's terms and conditions of purchase, including but not limited to the warranty expressed therein, which apply to these products.

No license, express or implied, by estoppel or otherwise, to any intellectual property rights is granted by this document or by any conduct of Vishay.

The products shown herein are not designed for use in medical, life-saving, or life-sustaining applications unless otherwise expressly indicated. Customers using or selling Vishay products not expressly indicated for use in such applications do so entirely at their own risk and agree to fully indemnify Vishay for any damages arising or resulting from such use or sale. Please contact authorized Vishay personnel to obtain written terms and conditions regarding products designed for such applications.

Product names and markings noted herein may be trademarks of their respective owners.

Document Number: 91000 Revision: 18-Jul-08

Mouser Electronics

Authorized Distributor

Click to View Pricing, Inventory, Delivery & Lifecycle Information:

Vishay:

DG200BDJ DG200BDJ-E3